SML150FB12

Attributes:
-aerospace build standard
-high reliability
-lightweight
-metal matrix base plate
-AlN isolation

Maximum rated values/Electrical Properties

Collector-emitter Voltage		V_{ce}	1200	V
DC Collector Current	Tc=70C, Tvj=175C Tc=25C,Tvj=175C	I_c, nom Ic	150 200	A
Repetitive peak Collector Current	tp=1msec,Tc=80C	I_{crm}	300	A
Total PowerDissipation	Tc=25C	P_{tot}	850	W
Gate-emitter peak voltage		V_{ges}	+/-20	V
DC Forward Diode Current		I_f	150	A
Repetitive Peak Forward Current	tp=1msec	I_{frm}	300	A
I^2t value per diode	Vr=0V, tp=10msec, Tvj=125C	I^2_t	4600	A^2sec
Isolation test voltage	RMS, 50Hz, t=1min	V_{isol}	2500	V

Collector-emitter saturation voltage	Ic=150A,Vge=15V, Tc=25C Ic=150A,Vge=15V,Tc=125C	$V_{ce(sat)}$		1.70 2.0	2.15	V V
Gate Threshold voltage	Ic=6.4mA,Vce=Vge, Tvj=25C	$Vge_{(th)}$	5.0	5.8	6.5	V
Input capacitance	f=1MHz,Tvj=25C,Vce=25V, Vge=0V	C_{ies}		10.5		nF
Reverse transfer Capacitance	f=1MHz,Tvj=25C,Vce=25V, Vge=0V	C_{res}		0.5		nF
Collector emitter cut off current	Vce=600V,Vge=0V,Tvj=25C Vce=600V,Vge=0V,Tvj=125C	I_{ces}		1 1	5	mA mA
Gate emitter cut off current	Vce=0V,Vge=20V,Tvj=25C	I_{ges}			400	nA

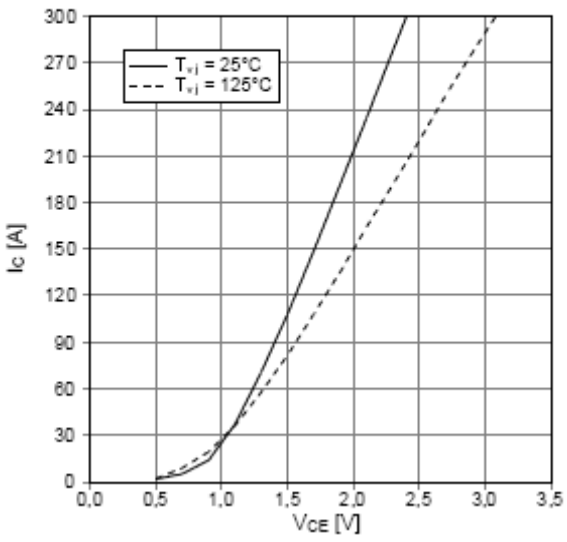
Turn on delay time	Ic=150A, Vcc=600V Vge=+/15V,Rg=8.2Ω,Tvj=25C Vge=+/-15V,Rg=8.2Ω,Tvj=125C	$t_{d,on}$		250 300		nsec nsec
Rise time	Ic=150A, Vcc=600V Vge=+/-15V,Rg=8.2Ω,Tvj=25C Vge=+/-15V,Rg=8.2Ω,Tvj=125C	tr		90 100		nsec nsec
Turn off delay time	Ic=150A, Vcc=600V Vge=+/-15V,Rg=8.2Ω,Tvj=25C Vge=+/-15V,Rg=8.2Ω,Tvj=125C	$t_{d,off}$		550 650		nsec nsec
Fall time	Ic=150A, Vcc=600V Vge=+/-15V,Rg=8.2Ω,Tvj=25C Vge=+/-15V,Rg=8.2Ω,Tvj=125C	t_f		130 160		nsec nsec
Turn energy loss per pulse	Ic=150A,Vce=600V,Vge=15V Rge=8.2Ω,L=80nH Tvj=125C	E_{on}		11		mJ
Turn off energy loss per pulse	Ic=150A,Vce=600V,Vge=15V Rge=8.2Ω,L=80nH Tvj=125C	E_{off}		24		mJ
SC Data	tp≤10µsec, Vge≤15V Vcc=900V, $Vce_{(max)}$=Vces-Lσdi/dt Tvj=125C	I_{sc}		600		A
Stray Module inductance		$L_{σce}$		40		nH
Terminal-chip resistance		R_c		1.2		mΩ

Diode characteristics

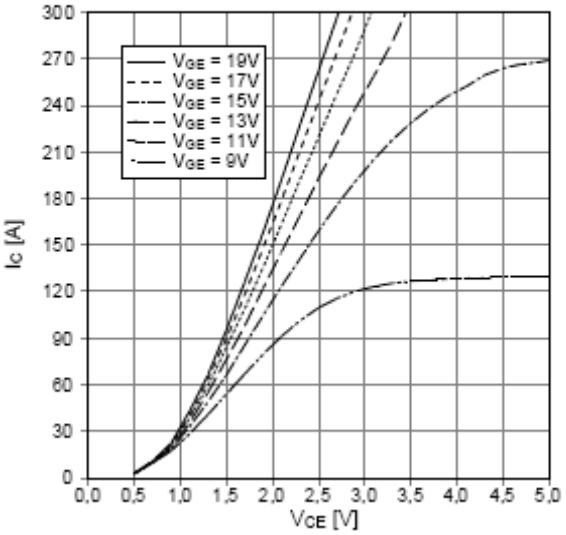
Forward voltage	Ic=150A,Vge=0V, Tc=25C Ic=150A,Vge=0V, Tc=125C	V_f		1.65 1.65	2.1	V V
Peak reverse recovery current	If=150A, -di/dt=1500A/µsec Vce=600V,Vge=-15V,Tvj=25C Vce=600V,Vge=-15V,Tvj=125C	I_{rm}		110 140		A A
Recovered charge	If=150A, -di/dt=1500A/µsec Vce=600V,Vge=-15V,Tvj=25C Vce=600V,Vge=-15V,Tvj=125C	Qr		15 28		µC µC
Reverse recovery energy	If=150A, -di/dt=1500A/µsec Vce=600V,Vge=-10V,Tvj=25C Vce=600V,Vge=-10V,Tvj=125C	E_{rec}		7.0 14		mJ mJ

Thermal Properties			Min	Typ	Max	
Thermal resistance junction to case	Igbt Diode	$R_{\theta J-C}$			0.15 0.26	K/W
Thermal resistance case to heatsink		$R_{\theta C-hs}$		0.03		K/W
Maximum junction temperature		Tvj			175	C
Maximum operating temperature		Top	-55		175	C
Storage Temperature		Tstg	-55		175	C

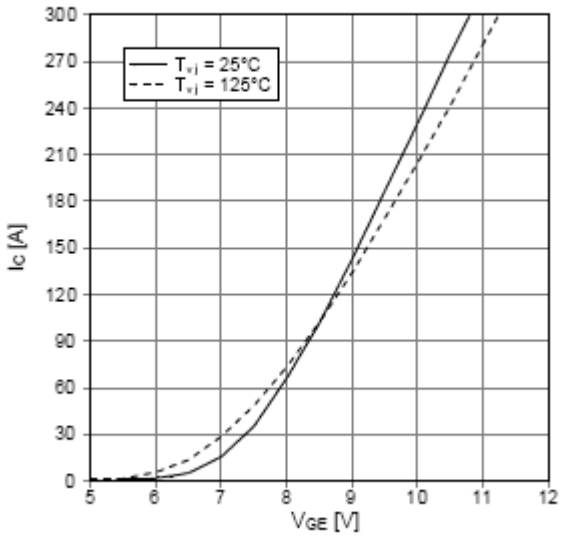
output characteristic IGBT-inverter (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



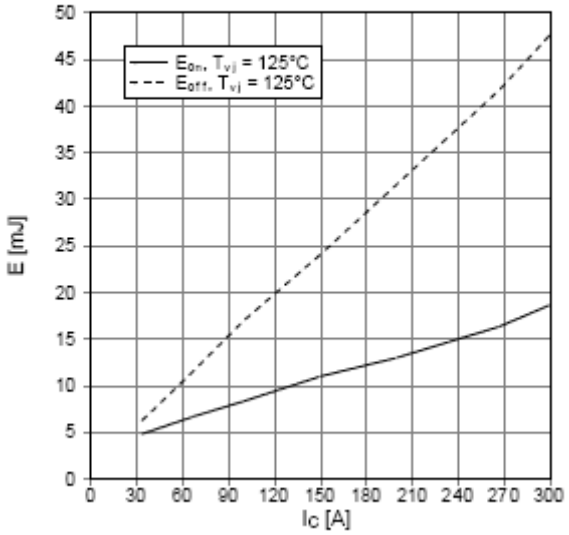
output characteristic IGBT-inverter (typical)
$I_C = f(V_{CE})$
$T_{vj} = 125°C$



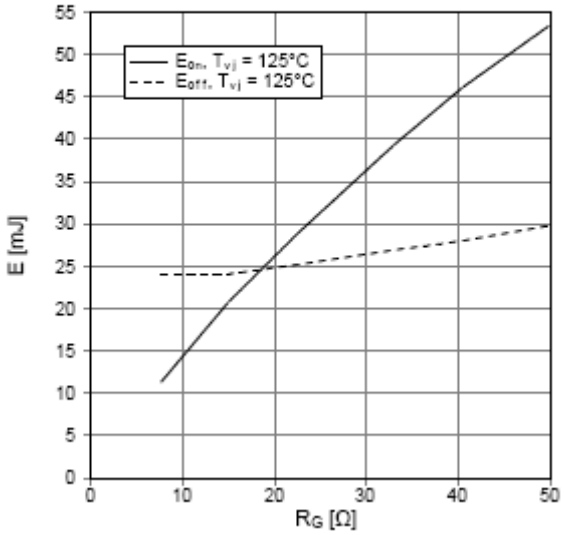
transfer characteristic IGBT-inverter (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



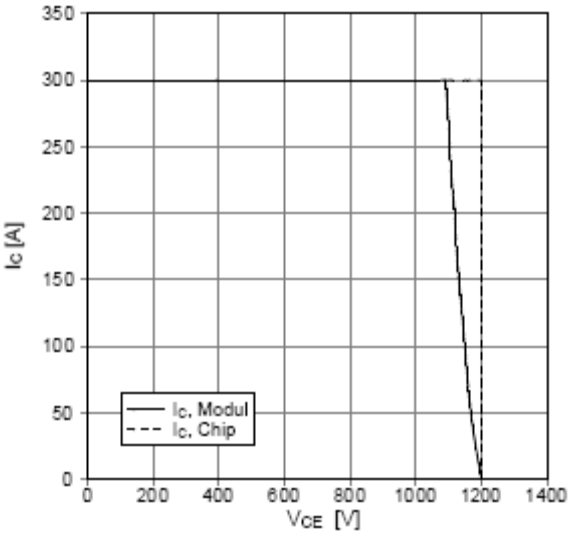
switching losses IGBT-inverter (typical)
E_{on} = f (I_C), E_{off} = f (I_C)
V_{GE} = ±15 V, R_{Gon} = 8,2 Ω, R_{Goff} = 8,2 Ω, V_{CE} = 600 V



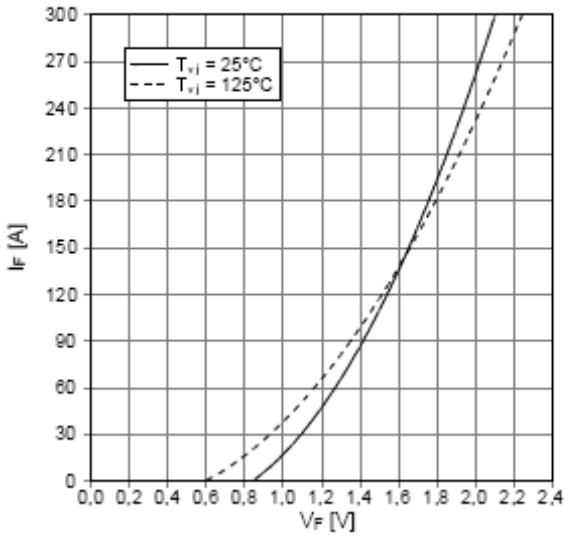
switching losses IGBT-Inverter (typical)
E_{on} = f (R_G), E_{off} = f (R_G)
V_{GE} = ±15 V, I_C = 150 A, V_{CE} = 600 V

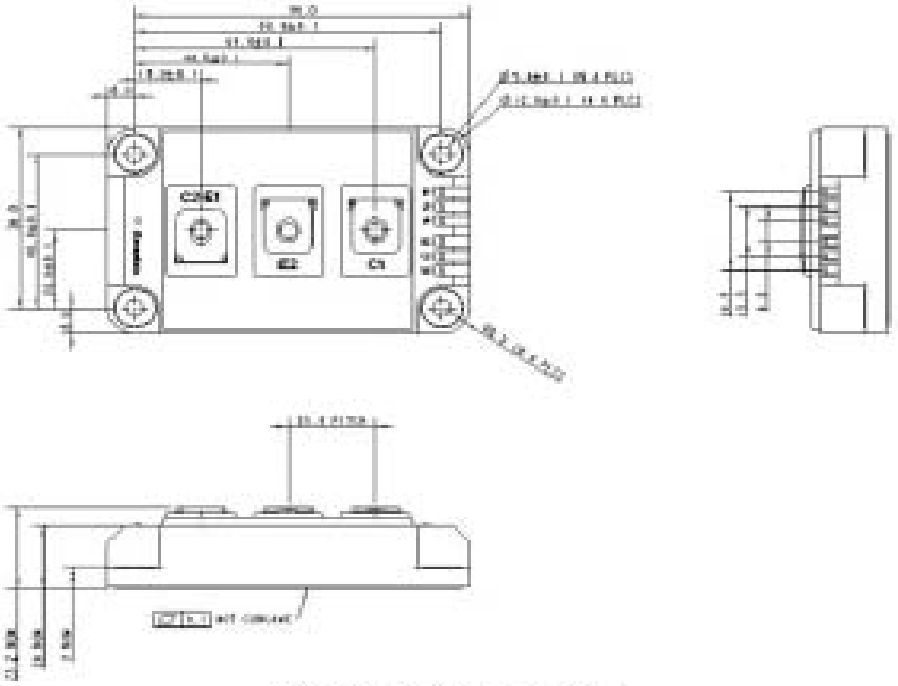


reverse bias safe operating area IGBT-inv. (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = \pm 15$ V, $R_{Goff} = 8{,}2\ \Omega$, $T_{vj} = 125°C$

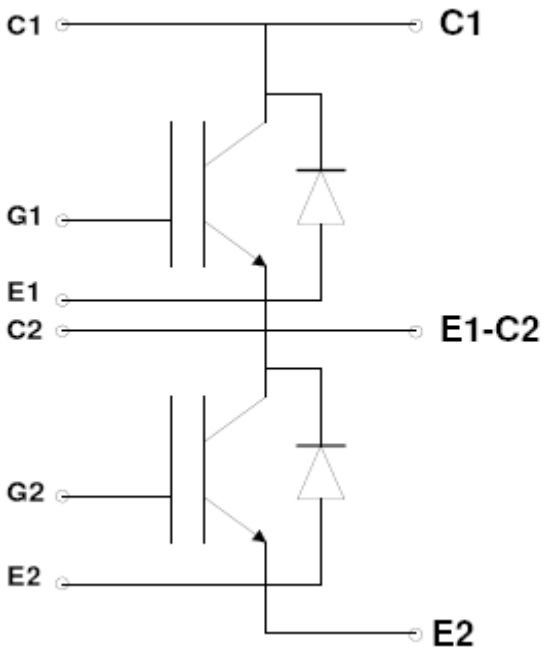


forward characteristic of diode-inverter (typical)
$I_F = f(V_F)$





All dimensions in mm



CIRCUIT DIAGRAM